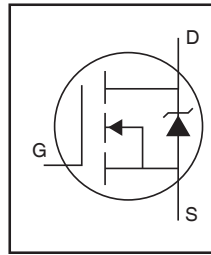


AUIRLS3114Z

HEXFET® Power MOSFET

Features

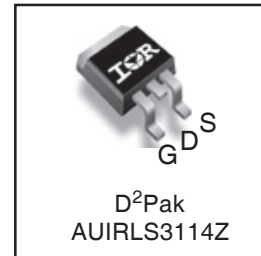
- Advanced Process Technology
- Ultra Low On-Resistance
- Enhanced dV/dT and dI/dT capability
- 175°C Operating Temperature
- Fast Switching
- Repetitive Avalanche Allowed up to Tjmax
- Lead-Free, RoHS Compliant
- Automotive Qualified *



V_{DSS}		40V
$R_{DS(on)}$	typ.	3.8mΩ
	max.	4.9mΩ
I_D (Silicon Limited)		122A ①
I_D (Wirebond Limited)		56A

Description

Specifically designed for Automotive applications, this HEXFET® Power MOSFET utilizes the latest processing techniques to achieve extremely low on-resistance per silicon area. Additional features of this design are a 175°C junction operating temperature, fast switching speed and improved repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in Automotive applications and a wide variety of other applications.



G	D	S
Gate	Drain	Source

Absolute Maximum Ratings

Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (T_A) is 25°C, unless otherwise specified.

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$ (Silicon Limited)	122①	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$ (Silicon Limited)	86 ①	
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$ (Wirebond Limited)	56	
I_{DM}	Pulsed Drain Current ②	488	
$P_D @ T_C = 25^\circ\text{C}$	Maximum Power Dissipation	143	W
	Linear Derating Factor	0.95	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS} (Thermally Limited)	Single Pulse Avalanche Energy ③	168	mJ
E_{AS} (Tested)	Single Pulse Avalanche Energy	518	
I_{AR}	Avalanche Current ②	See Fig. 12a, 12b, 15, 16	A
E_{AR}	Repetitive Avalanche Energy ②		mJ
dv/dt	Peak Diode Recovery ④	2.3	V/ns
T_J	Operating Junction and	-55 to + 175	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds (1.6mm from case)		

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ⑤	—	1.05	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB Mount) ⑦	—	40	

HEXFET® is a registered trademark of International Rectifier.

*Qualification standards can be found at <http://www.irf.com/>

Static Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	40	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.03	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$ Ⓣ
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	3.8	4.9	m Ω	$V_{GS} = 10V, I_D = 56A$ Ⓣ
$V_{GS(th)}$	Gate Threshold Voltage	1	1.7	2.5	V	$V_{DS} = V_{GS}, I_D = 100\mu A$
$\Delta V_{GS(th)}$	Gate Threshold Voltage Coefficient	—	-6.6	—	mV/ $^\circ\text{C}$	
g_{fs}	Forward Transconductance	103	—	—	S	$V_{DS} = 10V, I_D = 56A$
R_G	Internal Gate Resistance	—	0.8	—	Ω	
I_{DSS}	Drain-to-Source Leakage Current	—	—	20	μA	$V_{DS} = 40V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 40V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 16V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -16V$

Dynamic Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge	—	35	53	nC	$I_D = 56A$ $V_{DS} = 20V$ $V_{GS} = 4.5V$ Ⓣ
Q_{gs}	Gate-to-Source Charge	—	11	—		
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	16	—		
$t_{d(on)}$	Turn-On Delay Time	—	28	—	ns	$V_{DD} = 20V$ $I_D = 56A$ $R_G = 3.7\Omega$ $V_{GS} = 4.5V$ Ⓣ
t_r	Rise Time	—	271	—		
$t_{d(off)}$	Turn-Off Delay Time	—	43	—		
t_f	Fall Time	—	60	—		
C_{iss}	Input Capacitance	—	3617	—	pF	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1.0\text{MHz}$, See Fig. 5
C_{oss}	Output Capacitance	—	633	—		
C_{rss}	Reverse Transfer Capacitance	—	345	—		
C_{oss}	Output Capacitance	—	2378	—		
C_{oss}	Output Capacitance	—	570	—		
$C_{oss\ eff.}$	Effective Output Capacitance	—	875	—		

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	122	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) Ⓣ	—	—	488		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 56A, V_{GS} = 0V$ Ⓣ
t_{rr}	Reverse Recovery Time	—	33	50	ns	$T_J = 25^\circ\text{C}, I_F = 56A, V_{DD} = 20V,$ $di/dt = 100A/\mu s$ Ⓣ
Q_{rr}	Reverse Recovery Charge	—	32	48	nC	
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

- ① Calculated continuous current based on maximum allowable junction temperature. Bond wire current limit is 56A. Note that current limitations arising from heating of the device leads may occur with some lead mounting arrangements. (Refer to AN-1140)
- ② Repetitive rating; pulse width limited by max. junction temperature.
- ③ Limited by T_{Jmax} , starting $T_J = 25^\circ\text{C}$, $L = 0.107\text{mH}$, $R_G = 50\Omega$, $I_{AS} = 56A$, $V_{GS} = 10V$. Part not recommended for use above this value.

- ④ $I_{SD} \leq 56A$, $di/dt \leq 263A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 175^\circ\text{C}$.
- ⑤ Pulse width $\leq 1.0\text{ms}$; duty cycle $\leq 2\%$.
- ⑥ $C_{oss\ eff.}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .
- ⑦ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994.
- ⑧ R_{θ} is measured at T_J approximately 90°C

Qualification Information[†]

Qualification Level		Automotive (per AEC-Q101) ^{††}	
		Comments: This part number(s) passed Automotive qualification. IR's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.	
Moisture Sensitivity Level		3L-D2 PAK	MSL1
ESD	Machine Model	Class M4(+/- 600V) ^{†††} (per AEC-Q101-002)	
	Human Body Model	Class H1C(+/- 2000V) ^{†††} (per AEC-Q101-001)	
	Charged Device Model	Class C5(+/- 2000V) ^{†††} (per AEC-Q101-005)	
RoHS Compliant		Yes	

† Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/>

†† Exceptions (if any) to AEC-Q101 requirements are noted in the qualification report.

††† Highest passing voltage

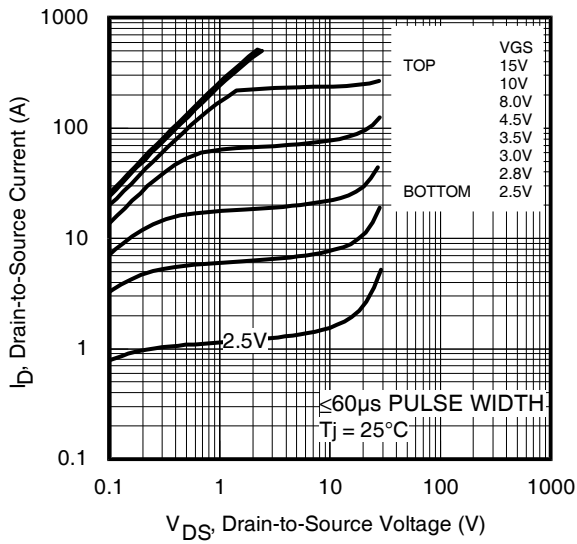


Fig 1. Typical Output Characteristics

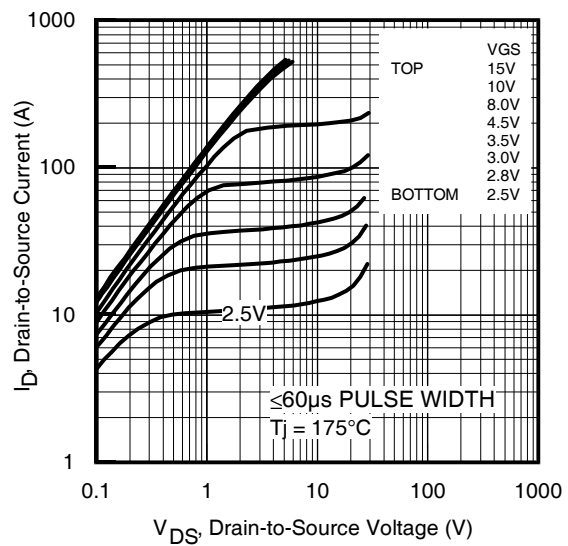


Fig 2. Typical Output Characteristics

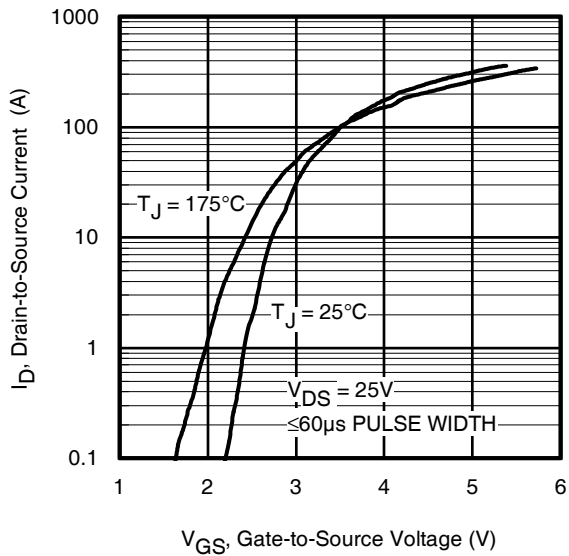


Fig 3. Typical Transfer Characteristics

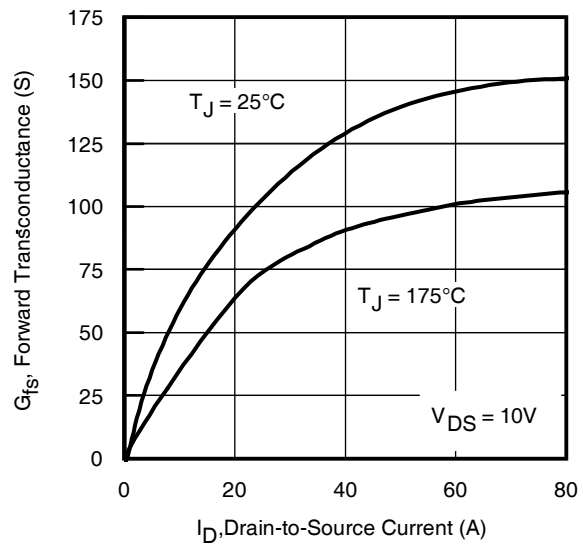


Fig 4. Typical Forward Transconductance vs. Drain Current

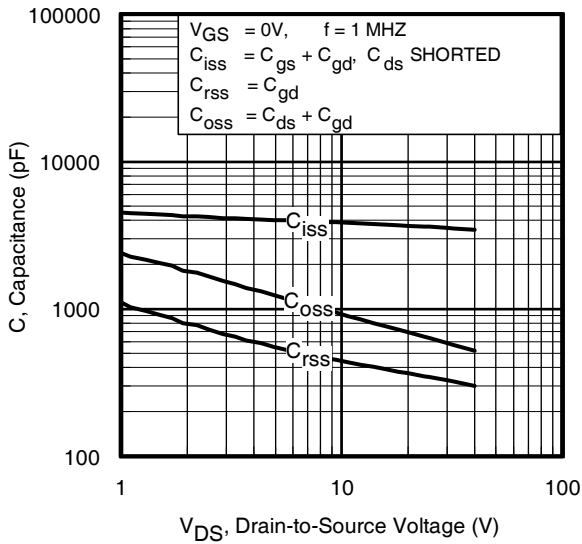


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

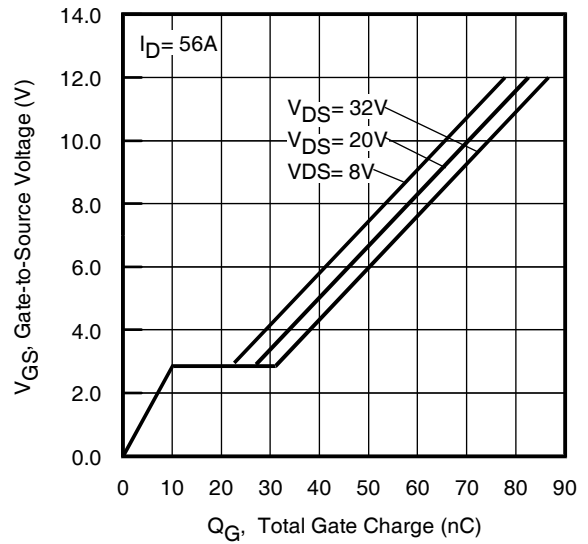


Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

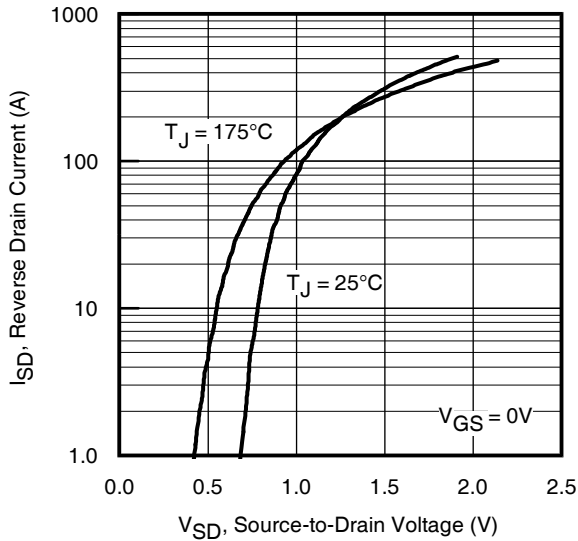


Fig 7. Typical Source-Drain Diode Forward Voltage

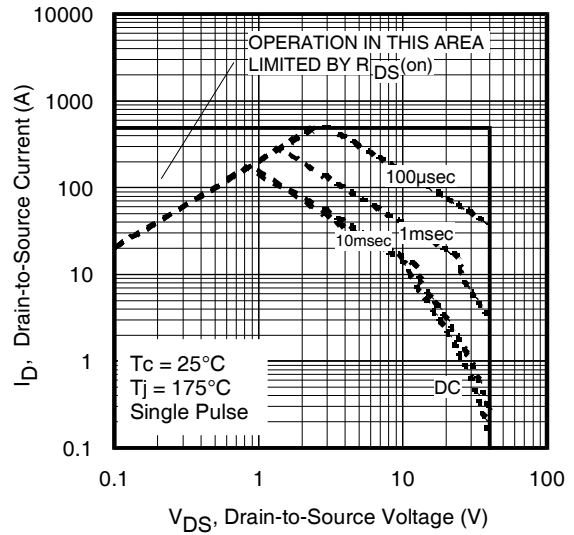


Fig 8. Maximum Safe Operating Area

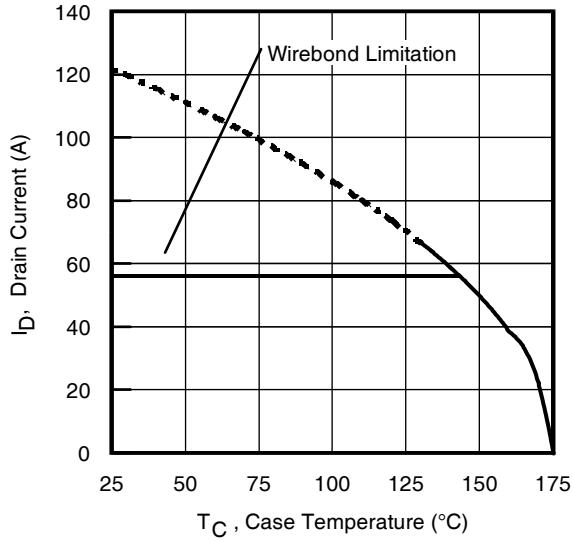


Fig 9. Maximum Drain Current vs. Case Temperature

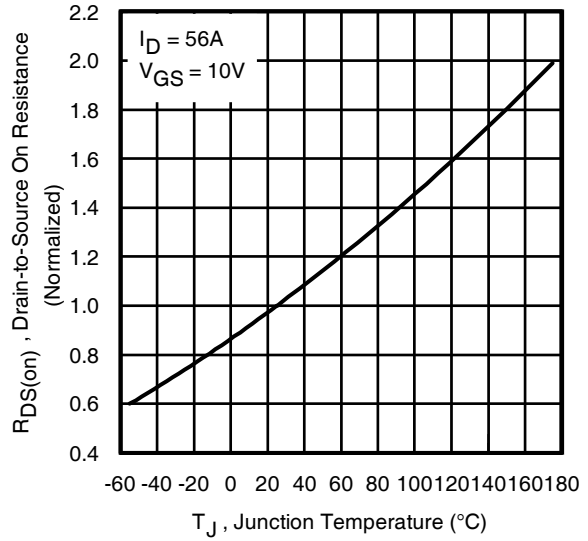


Fig 10. Normalized On-Resistance vs. Temperature

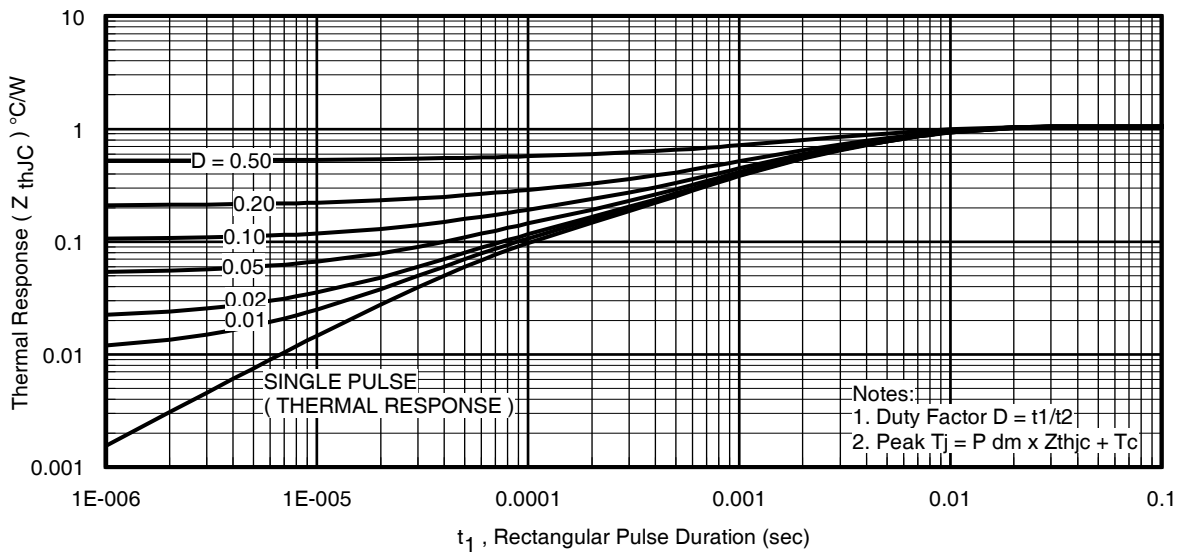


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

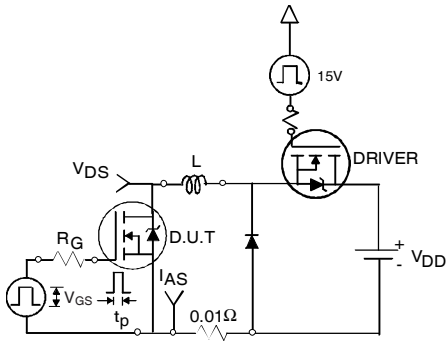


Fig 12a. Unclamped Inductive Test Circuit

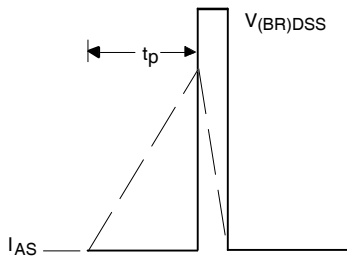


Fig 12b. Unclamped Inductive Waveforms

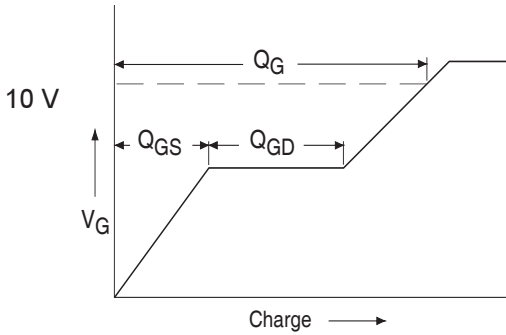


Fig 13a. Basic Gate Charge Waveform

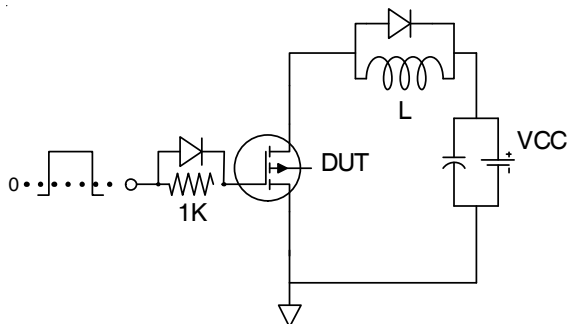


Fig 13b. Gate Charge Test Circuit
www.irf.com

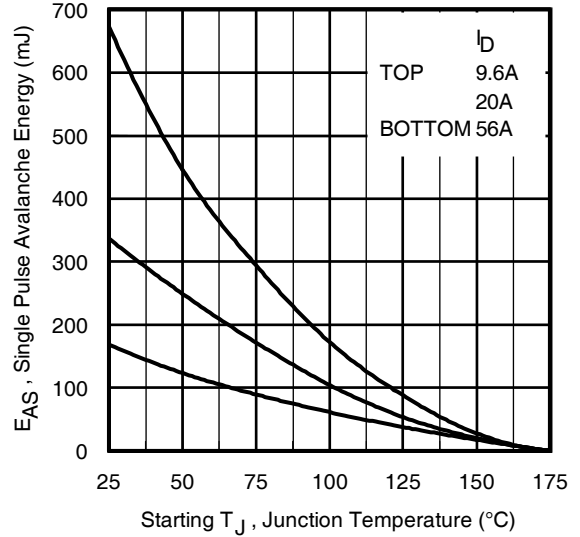


Fig 12c. Maximum Avalanche Energy vs. Drain Current

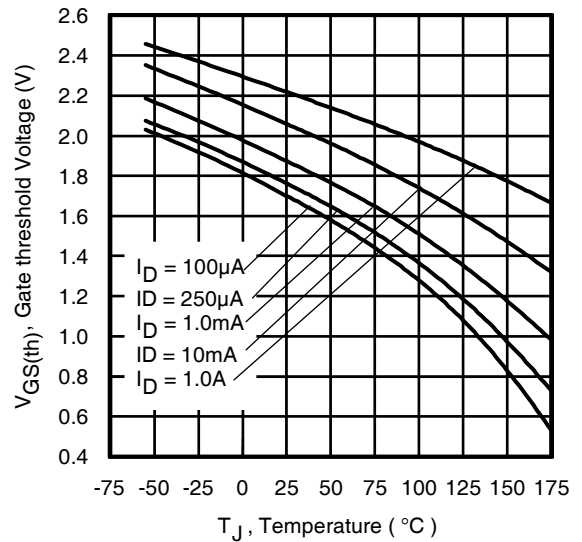


Fig 14. Threshold Voltage vs. Temperature

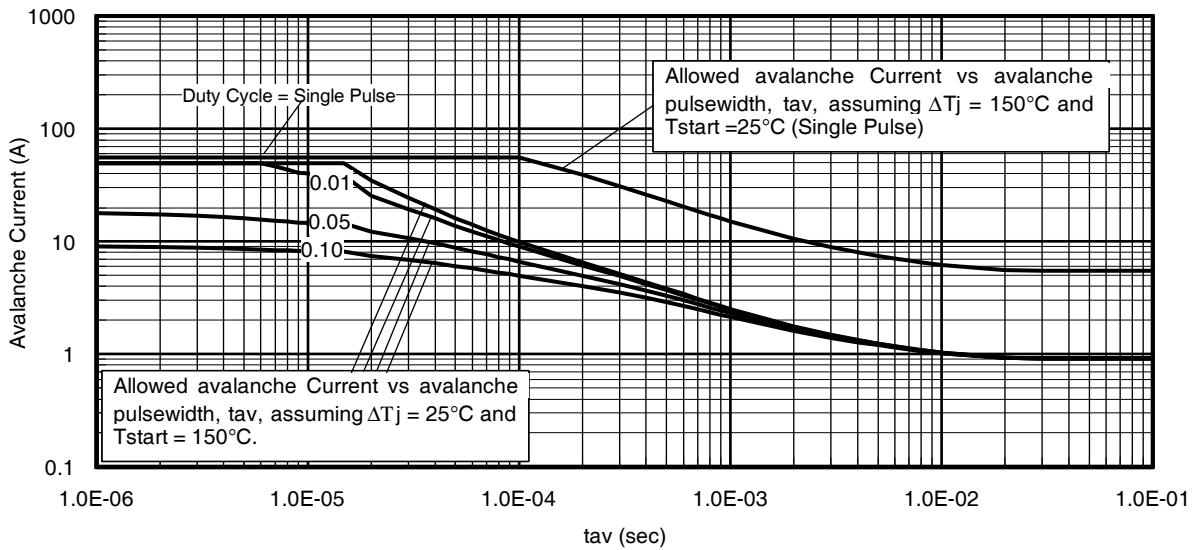


Fig 15. Typical Avalanche Current vs.Pulsewidth

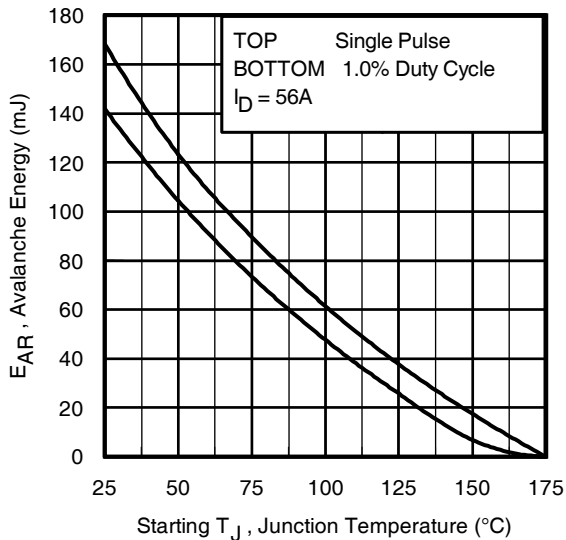


Fig 16. Maximum Avalanche Energy vs. Temperature

**Notes on Repetitive Avalanche Curves , Figures 15, 16:
(For further info, see AN-1005 at www.irf.com)**

1. Avalanche failures assumption:
Purely a thermal phenomenon and failure occurs at a temperature far in excess of T_{jmax} . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as ΔT_{jmax} is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 12a, 12b.
4. $P_{D(ave)}$ = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6. I_{av} = Allowable avalanche current.
7. ΔT = Allowable rise in junction temperature, not to exceed T_{jmax} (assumed as 25°C in Figure 15, 16).
 t_{av} = Average time in avalanche.
 D = Duty cycle in avalanche = $t_{av} \cdot f$
 $Z_{thJC}(D, t_{av})$ = Transient thermal resistance, see figure 11)

$$P_{D(ave)} = 1/2 (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC}$$

$$I_{av} = 2 \Delta T / [1.3 \cdot BV \cdot Z_{th}]$$

$$E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$$

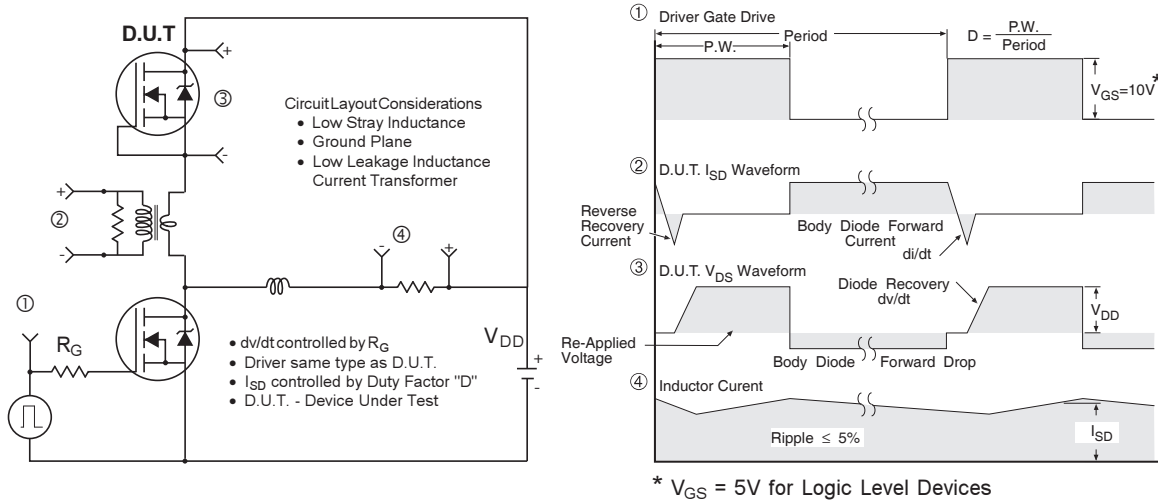


Fig 17. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

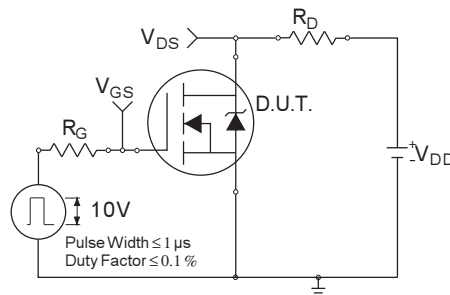


Fig 18a. Switching Time Test Circuit

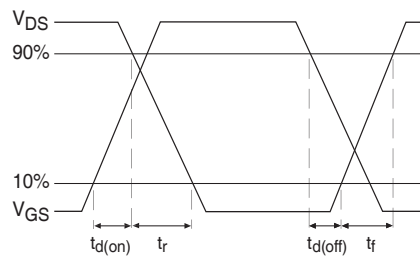
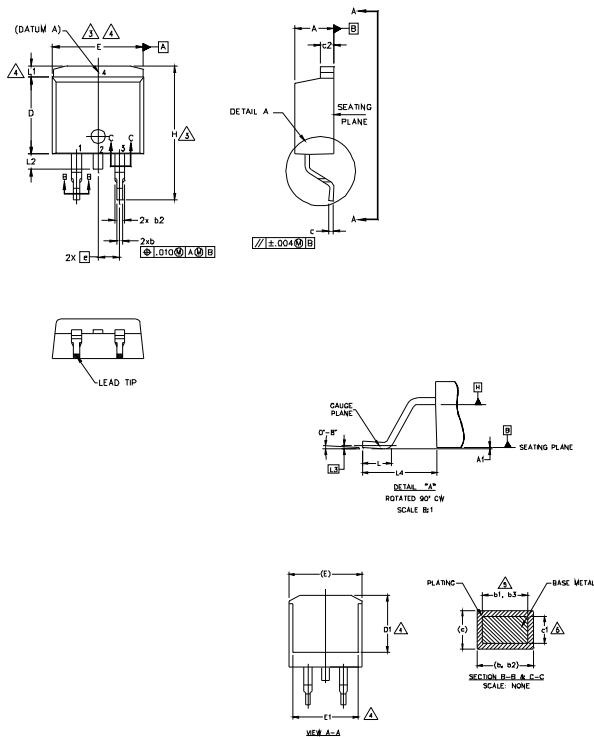


Fig 18b. Switching Time Waveforms

D²Pak Package Outline (Dimensions are shown in millimeters (inches))



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
 2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
 3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY AT DATUM H.
 4. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSION E, L1, D1 & E1.
 5. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
 6. DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
 7. CONTROLLING DIMENSION: INCH.
 8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-263AB.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	5
A1	0.00	0.254	.000	.010	
b	0.51	0.99	.020	.039	5
b1	0.51	0.89	.020	.035	
b2	1.14	1.78	.045	.070	5
b3	1.14	1.73	.045	.068	
c	0.38	0.74	.015	.029	5
c1	0.38	0.58	.015	.023	
c2	1.14	1.65	.045	.065	3
D	8.38	9.65	.330	.380	
D1	6.86	-	.270	-	4
E	9.65	10.67	.380	.420	3,4
E1	6.22	-	.245	-	4
e	2.54 BSC		.100 BSC		4
H	14.61	15.88	.575	.625	
L	1.78	2.79	.070	.110	4
L1	-	1.65	-	.066	
L2	1.27	1.78	-	.070	
L3	0.25 BSC		.010 BSC		
L4	4.78	5.28	.188	.208	

LEAD ASSIGNMENTS

HEXFET

- 1.- GATE
- 2, 4.- DRAIN
- 3.- SOURCE

IGBTs, CoPACK

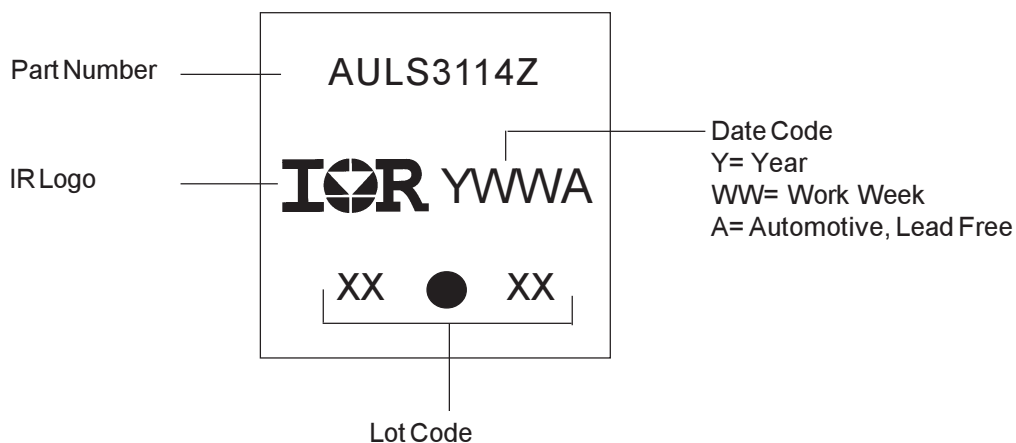
- 1.- GATE
- 2, 4.- COLLECTOR
- 3.- EMITTER

DIODES

- 1.- ANODE *
- 2, 4.- CATHODE
- 3.- ANODE

* PART DEPENDENT.

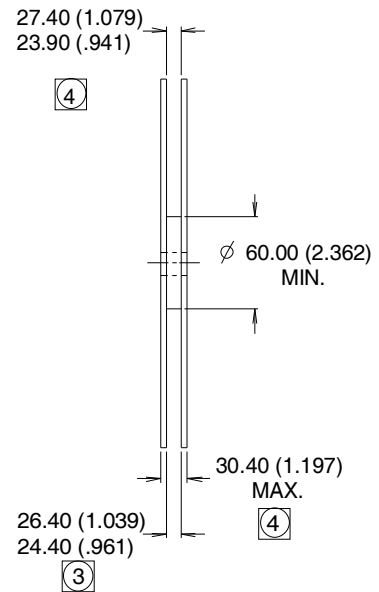
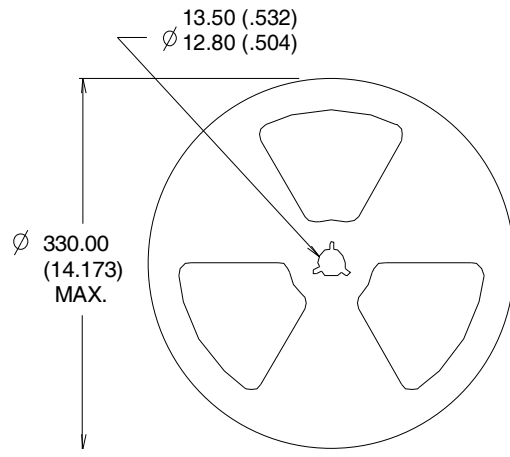
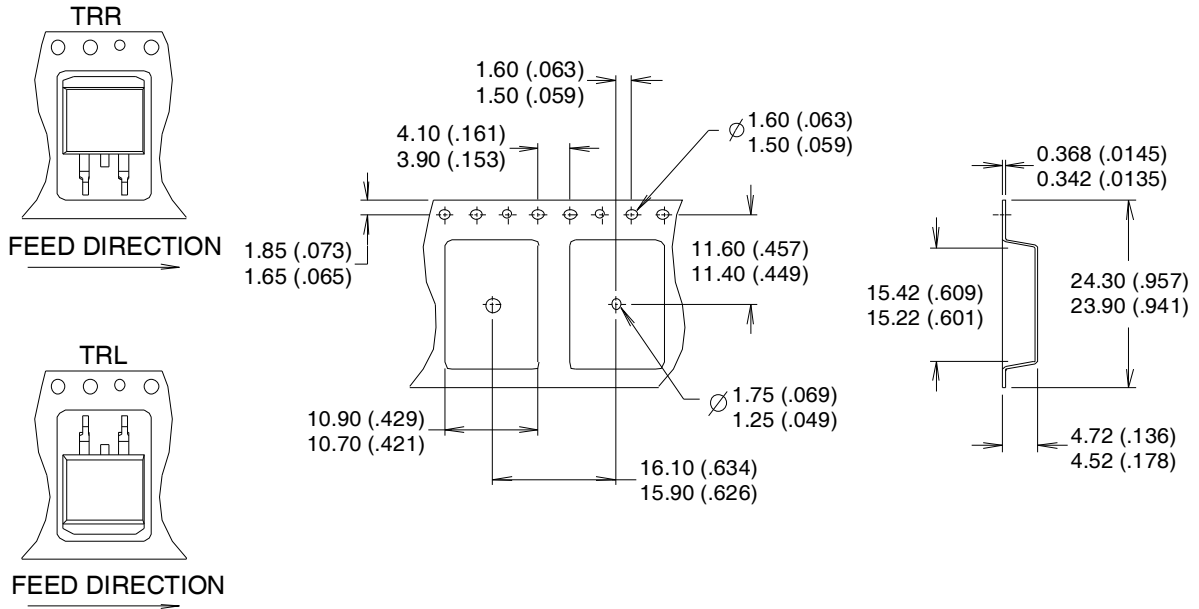
D²Pak Part Marking Information



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

D²Pak (TO-263AB) Tape & Reel Information

Dimensions are shown in millimeters (inches)



- NOTES :
1. COMFORMS TO EIA-418.
 2. CONTROLLING DIMENSION: MILLIMETER.
 - ③ DIMENSION MEASURED @ HUB.
 - ④ INCLUDES FLANGE DISTORTION @ OUTER EDGE.

Ordering Information

Base part	Package Type	Standard Pack		Complete Part Number
		Form	Quantity	
AUIRLS3114Z	D2Pak	Tube	50	AUIRLS3114Z
		Tape and Reel Left	800	AUIRLS3114ZTRL
		Tape and Reel Right	800	AUIRLS3114ZTRR

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For technical support, please contact IR's Technical Assistance Center
<http://www.irf.com/technical-info/>

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